BCR3KM-12LB

Triac

Low Power Use

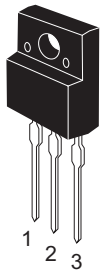
REJ03G0314-0100
Rev.1.00
Aug.20.2004

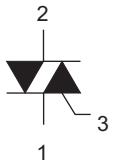
Features

- $I_{T\,(RMS)}$: 3 A
- V_{DRM} : 600 V
- I_{FGTI}, I_{RGTI}, I_{RGTIII} : 20 mA (10 mA)[Note5]
- Viso : 2000 V
- The product guaranteed maximum junction temperature of 150°C.
- Insulated Type
- Planar Passivation Type
- Refer to the recommended circuit values around the triac before using.

Outline

TO-220FN





1. T_1 Terminal
2. T_2 Terminal
3. Gate Terminal

Applications

Switching mode power supply, small motor control, heater control, solenoid driver, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage[Note1]	V_{DRM}	600	V
Non-repetitive peak off-state voltage[Note1]	V_{DSM}	720	V

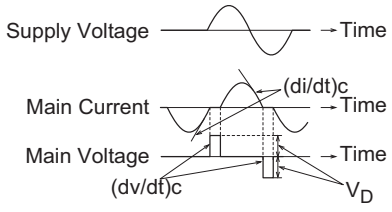
Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T\ (RMS)}$	3	A	Commercial frequency, sine full wave 360° conduction, Tc = 134°C
Surge on-state current	I_{TSM}	30	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	3.7	A^2s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	3	W	
Average gate power dissipation	$P_{G\ (AV)}$	0.3	W	
Peak gate voltage	V_{GM}	6	V	
Peak gate current	I_{GM}	0.5	A	
Junction temperature	Tj	– 40 to +150	°C	
Storage temperature	Tstg	– 40 to +150	°C	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

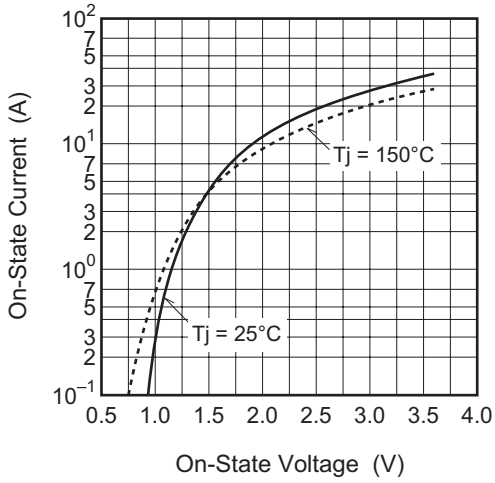
Parameter		Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current		I_{DRM}	—	—	2.0	mA	Tj = 150°C, V_{DRM} applied
On-state voltage		V_{TM}	—	—	1.5	V	Tc = 25°C, I_{TM} = 4.5 A, Instantaneous measurement
Gate trigger voltage[Note2]	I	V_{FGTI}	—	—	1.5	V	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	V_{RGTI}	—	—	1.5	V	
	III	V_{RGTIII}	—	—	1.5	V	
Gate trigger current[Note2]	I	I_{FGTI}	—	—	20[Note5]	mA	Tj = 25°C, V_D = 6 V, R_L = 6 Ω, R_G = 330 Ω
	II	I_{RGTI}	—	—	20[Note5]	mA	
	III	I_{RGTIII}	—	—	20[Note5]	mA	
Gate non-trigger voltage		V_{GD}	0.2/0.1	—	—	V	Tj = 125°C/150°C, V_D = 1/2 V_{DRM}
Thermal resistance		$R_{th\ (j-c)}$	—	—	4.0	°C/W	Junction to case[Note3]
Critical-rate of rise of off-state commutating voltage[Note4]		(dv/dt)c	5/1	—	—	V/µs	Tj = 125°C/150°C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.
3. The contact thermal resistance $R_{th\ (c-f)}$ in case of greasing is 0.5°C/W.
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
5. High sensitivity ($I_{GT} \leq 10$ mA) is also available. (I_{GT} item: 1)

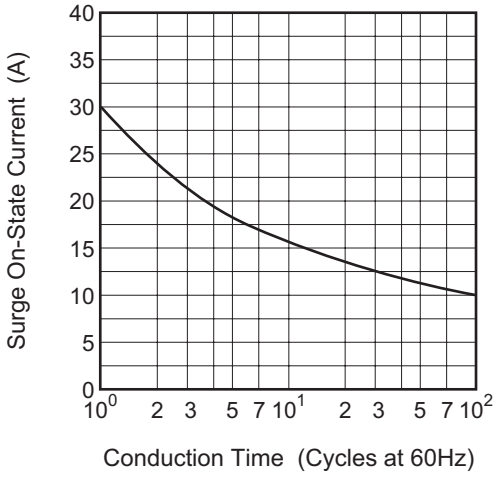
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C/150°C 2. Rate of decay of on-state commutating current (di/dt)c = –1.5 A/ms 3. Peak off-state voltage V_D = 400 V	

Performance Curves

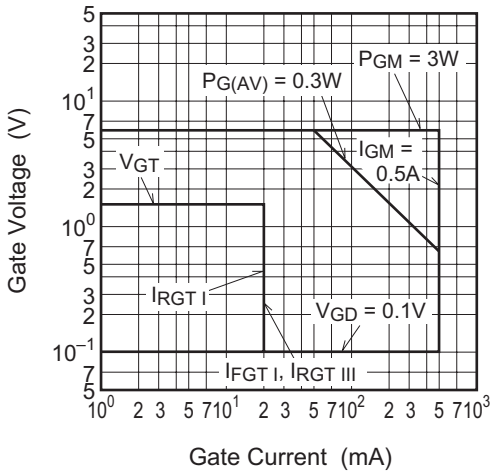
Maximum On-State Characteristics



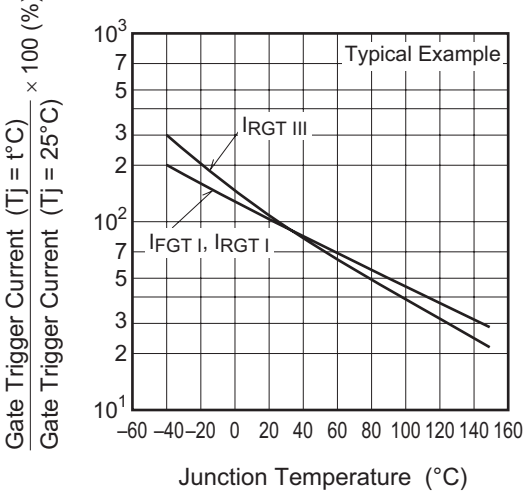
Rated Surge On-State Current



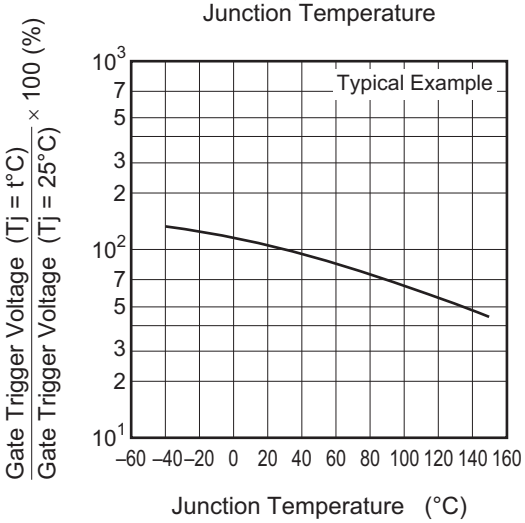
Gate Characteristics (I, II and III)



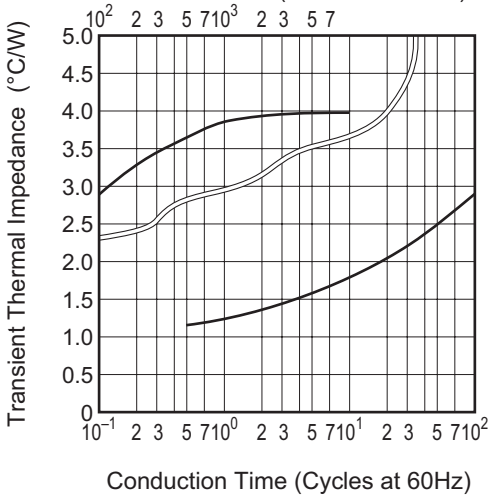
Gate Trigger Current vs. Junction Temperature



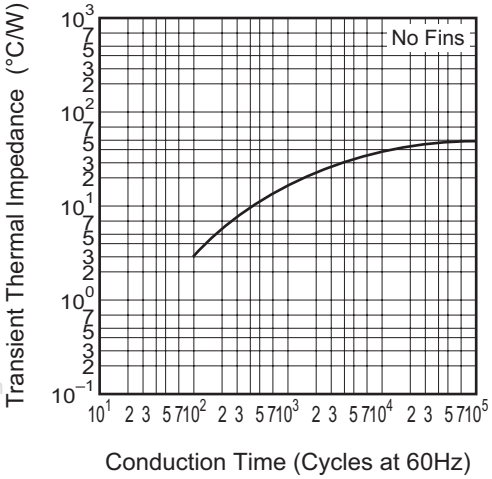
Gate Trigger Voltage vs. Junction Temperature



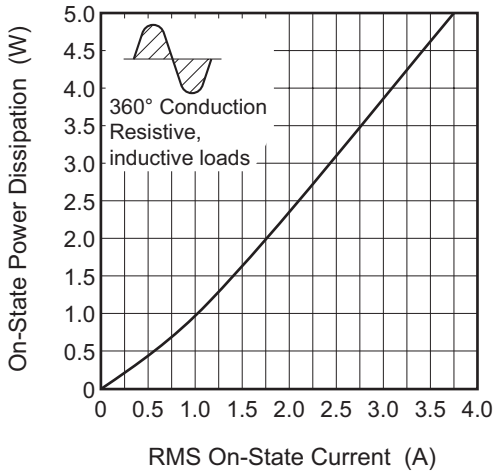
Maximum Transient Thermal Impedance Characteristics (Junction to case)



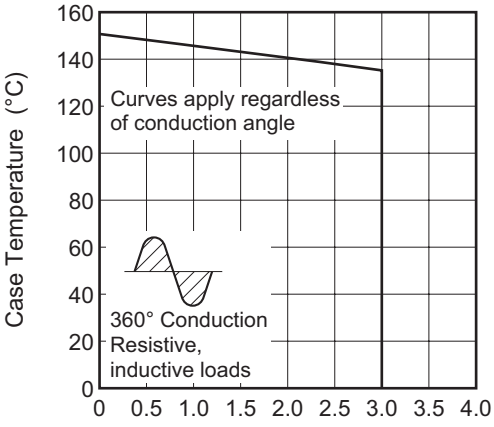
Maximum Transient Thermal Impedance Characteristics (Junction to ambient)



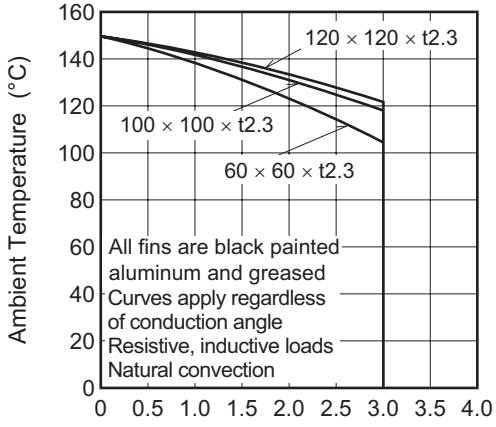
Maximum On-State Power Dissipation



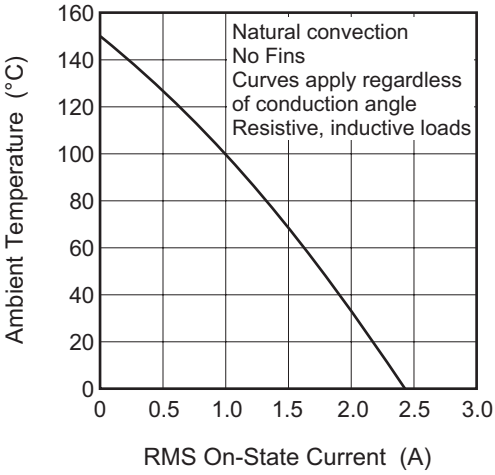
Allowable Case Temperature vs. RMS On-State Current



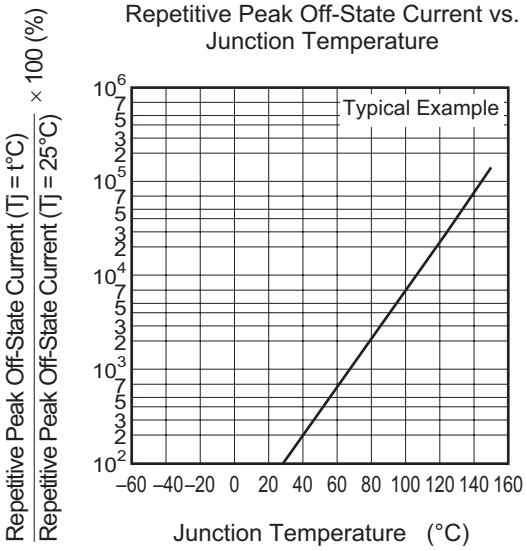
Allowable Ambient Temperature vs. RMS On-State Current



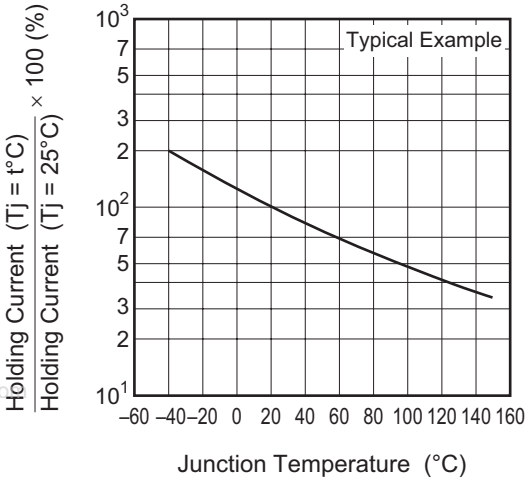
Allowable Ambient Temperature vs. RMS On-State Current



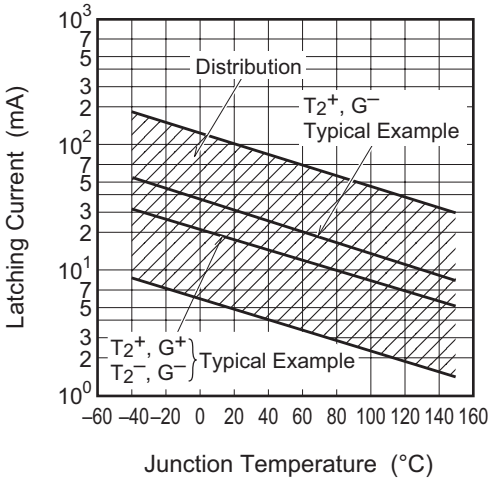
Repetitive Peak Off-State Current vs. Junction Temperature



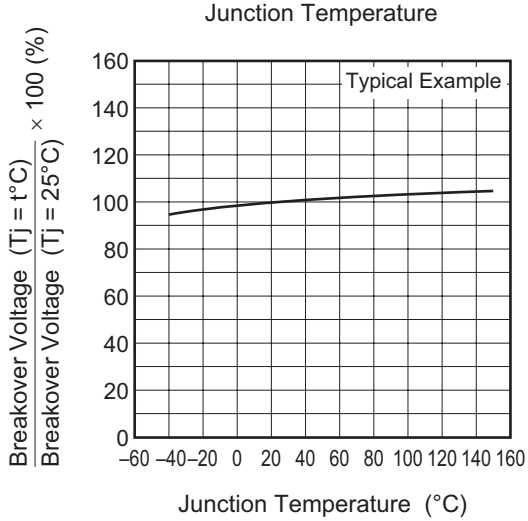
Holding Current vs.
Junction Temperature



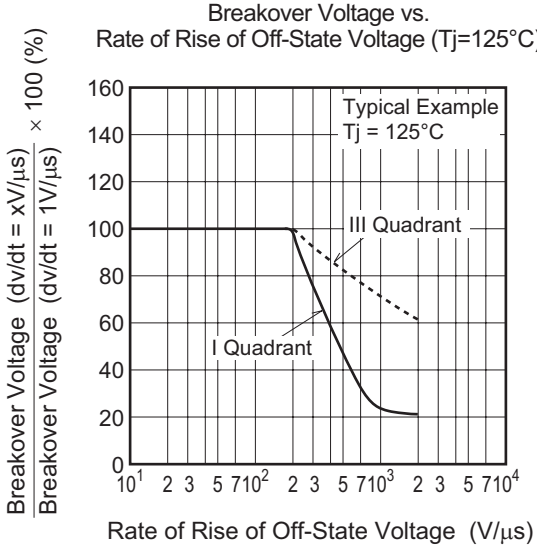
Latching Current vs.
Junction Temperature



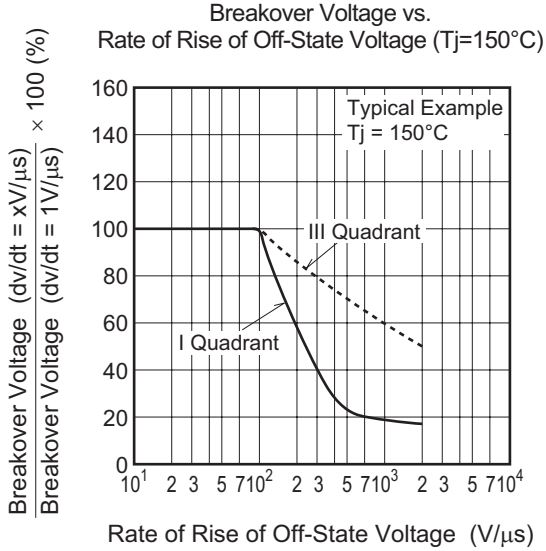
Breakover Voltage vs.
Junction Temperature



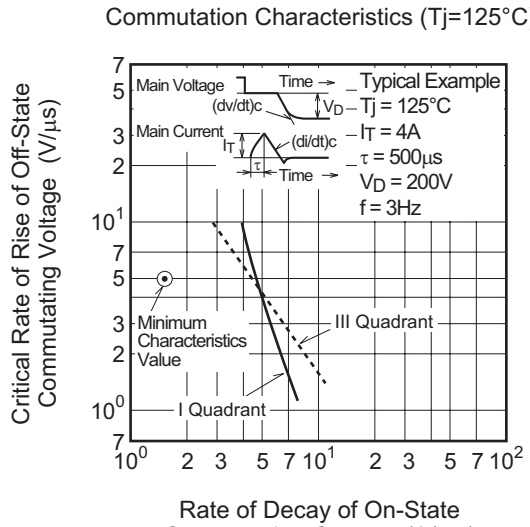
Breakover Voltage vs.
Rate of Rise of Off-State Voltage (Tj=125°C)



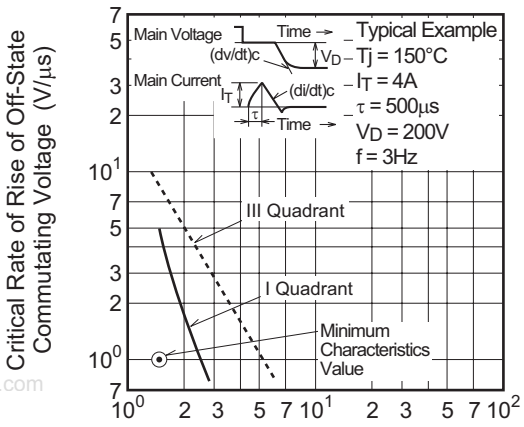
Breakover Voltage vs.
Rate of Rise of Off-State Voltage (Tj=150°C)



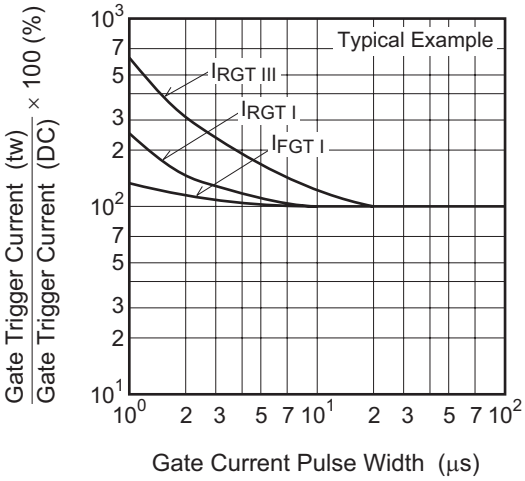
Commutation Characteristics (Tj=125°C)



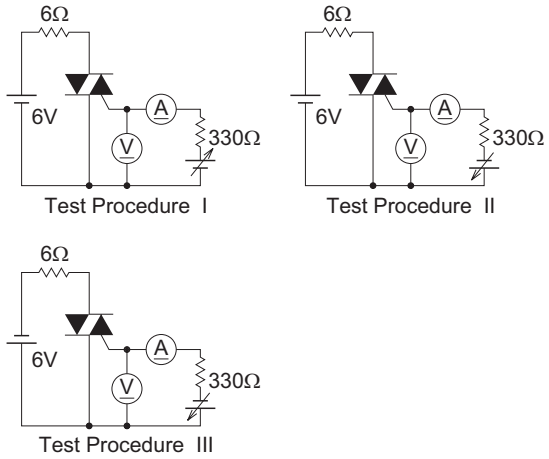
Commutation Characteristics (Tj=150°C)



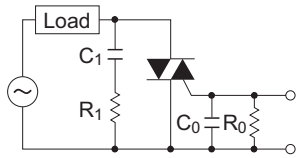
Gate Trigger Current vs. Gate Current Pulse Width



Gate Trigger Characteristics Test Circuits



Recommended Circuit Values Around The Triac

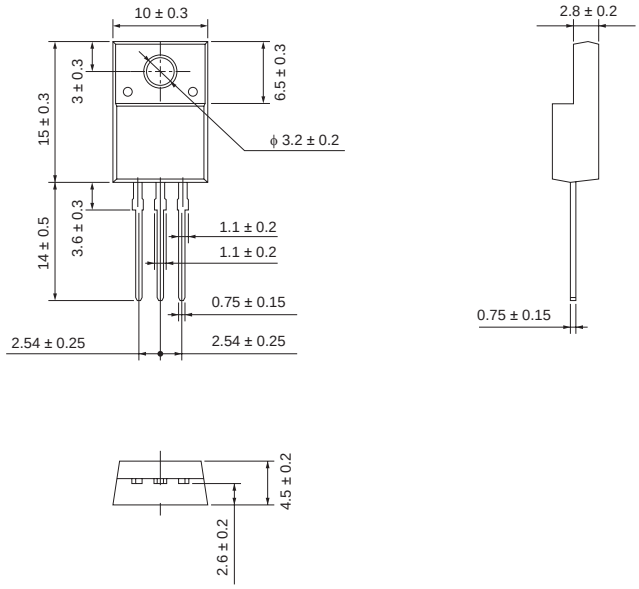


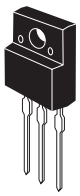
C_1 = 0.1 to 0.47µF C_0 = 0.1µF
R_1 = 47 to 100Ω R_0 = 100Ω

Package Dimensions

TO-220FN

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	—	2.0	Cu alloy





Symbol	Dimension in Millimeters		
	Min	Typ	Max
A			
A_1			
A_2			
b			
D			
E			
e			
x			
y			
y_1			
ZD			
ZE			

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	BCR3KM-12LB
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR3KM-12LB-A8

Note : Please confirm the specification about the shipping in detail.

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